



## Description

The SI4116DY-T1-E3 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

## General Features

$V_{DS} = 30V$   $I_D = 15A$

$R_{DS(ON)} < 9m\Omega$  @  $V_{GS}=10V$

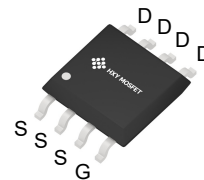
$R_{DS(ON)} < 14m\Omega$  @  $V_{GS}=4.5V$

## Application

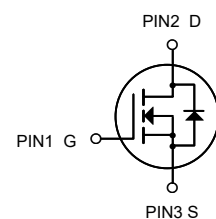
Battery protection

Load switch

Uninterruptible power supply



SOP-8  
(SO-8)



N-Channel MOSFET

## Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SI4116DY-T1-E3	SOP-8(SO-8)	HXY MOSFET	3000

## Absolute Maximum Ratings ( $T_c=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-Continuous	15.0	A
$I_D(70^{\circ}C)$	Drain Current-Continuous( $T_c=70^{\circ}C$ )	8.2	A
$I_{DM}$	Pulsed Drain Current	42	A
$P_D$	Maximum Power Dissipation	1.5	W
$E_{AS}$	Single pulse avalanche energy (Note 5)	62	mJ
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}C$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 2)	36	$^{\circ}C/W$



**Electrical Characteristics ( $T_J=25^{\circ}\text{C}$ , unless otherwise noted)**

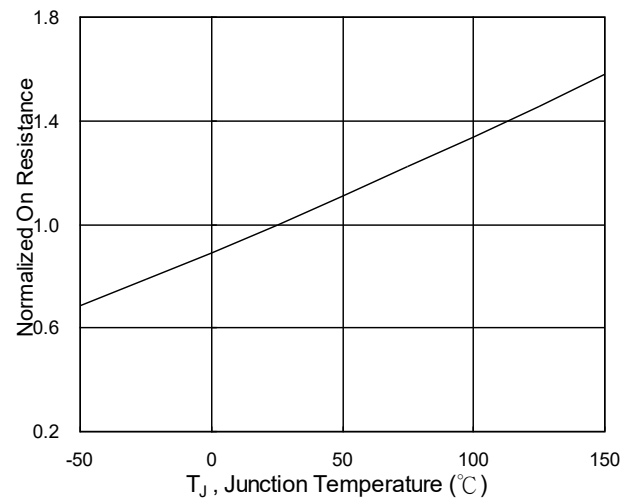
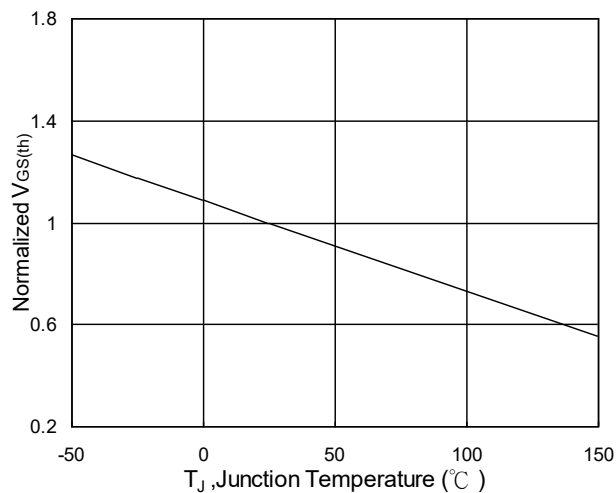
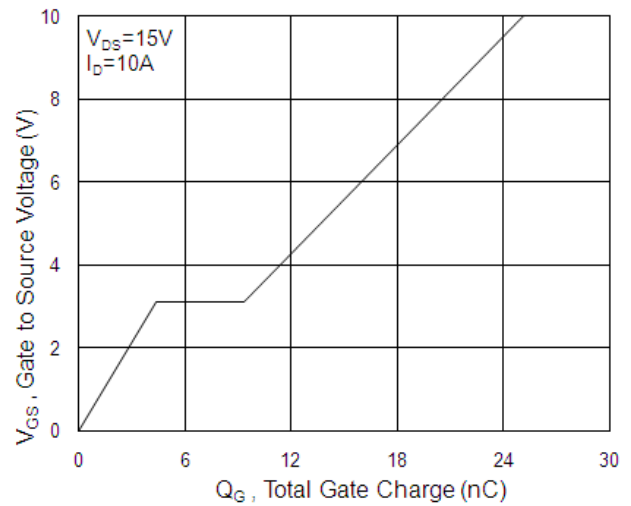
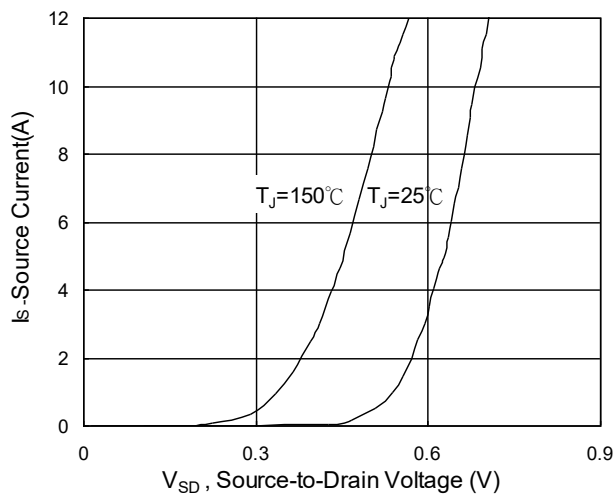
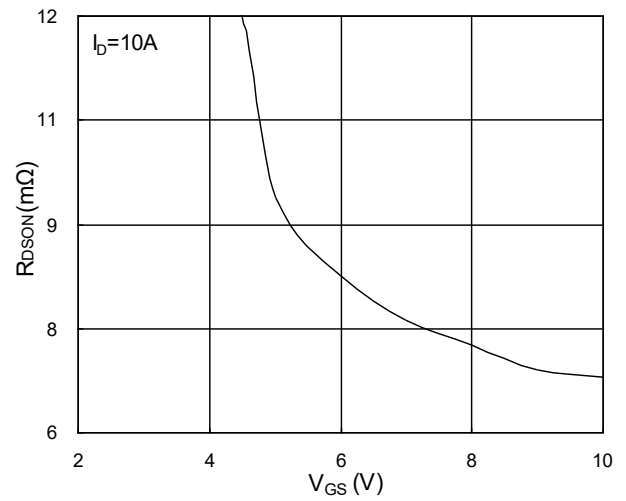
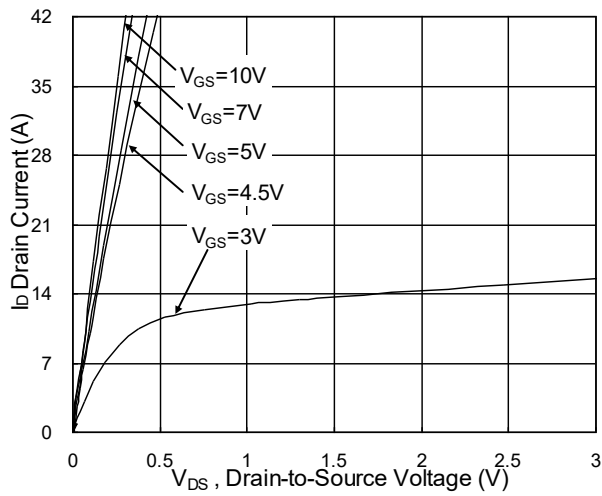
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V$ , $I_D=250\mu A$	30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to $25^{\circ}\text{C}$ , $I_D=1mA$	---	0.027	---	$V/^{\circ}\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V$ , $I_D=10A$	---	7.5	9	$m\Omega$
		$V_{GS}=4.5V$ , $I_D=8A$	---	11	14	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_D=250\mu A$	1.2	1.5	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.8	---	$mV/^{\circ}\text{C}$
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=24V$ , $V_{GS}=0V$ , $T_J=25^{\circ}\text{C}$	---	---	1	$\mu A$
		$V_{DS}=24V$ , $V_{GS}=0V$ , $T_J=55^{\circ}\text{C}$	---	---	5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V$ , $V_{DS}=0V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=5V$ , $I_D=10A$	---	5.8	---	S
$R_g$	Gate Resistance	$V_{DS}=0V$ , $V_{GS}=0V$ , $f=1MHz$	---	2.2	3.8	$\Omega$
$Q_g$	Total Gate Charge (4.5V)	$V_{DS}=15V$ , $V_{GS}=4.5V$ , $I_D=10A$	---	12.6	17.6	nC
$Q_{gs}$	Gate-Source Charge		---	4.2	5.9	
$Q_{gd}$	Gate-Drain Charge		---	5.1	7.1	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V$ , $V_{GS}=10V$ , $R_G=3.3\Omega$ $I_D=10A$	---	6.2	12.4	ns
$T_r$	Rise Time		---	59	106	
$T_{d(off)}$	Turn-Off Delay Time		---	27.6	55	
$T_f$	Fall Time		---	8.4	16.8	
$C_{iss}$	Input Capacitance	$V_{DS}=15V$ , $V_{GS}=0V$ , $f=1MHz$	---	1317	1845	pF
$C_{oss}$	Output Capacitance		---	163	228.2	
$C_{rss}$	Reverse Transfer Capacitance		---	131	183.4	
$I_S$	Continuous Source Current <sup>1,5</sup>	$V_G=V_D=0V$ , Force Current	---	---	15	A
$I_{SM}$	Pulsed Source Current <sup>2,5</sup>		---	---	42	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V$ , $I_S=1A$ , $T_J=25^{\circ}\text{C}$	---	---	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F=10A$ , $dI/dt=100A/\mu s$ , $T_J=25^{\circ}\text{C}$	---	12.5	---	nS
$Q_{rr}$	Reverse Recovery Charge		---	5	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{DD}=25V$ ,  $V_{GS}=10V$ ,  $L=0.1mH$ ,  $I_{AS}=35A$
- 4.The power dissipation is limited by  $150^{\circ}\text{C}$  junction temperature
- 5.The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.



## Typical Characteristics



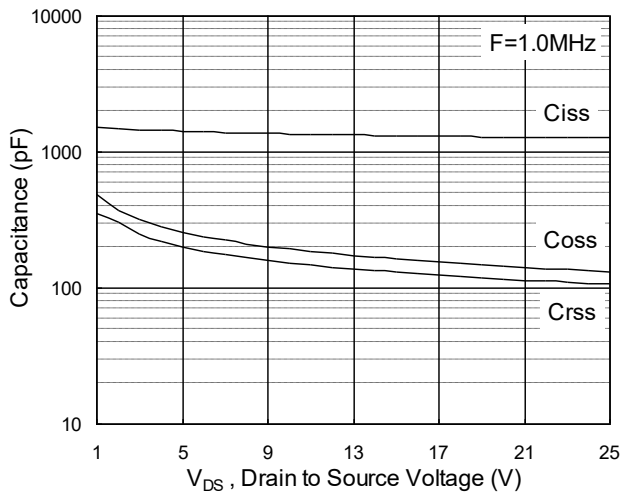


Fig.7 Capacitance

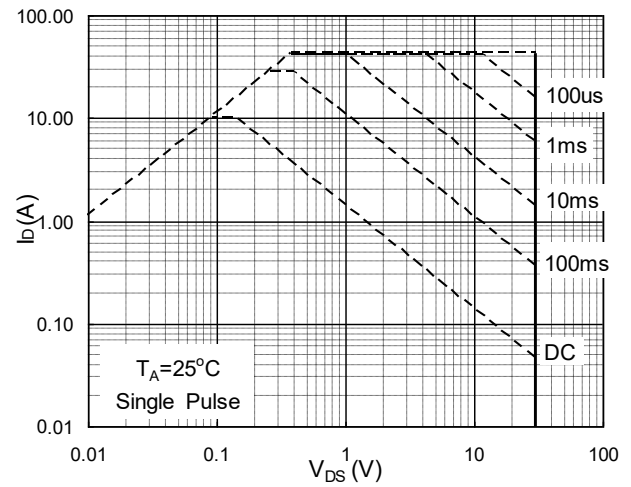


Fig.8 Safe Operating Area

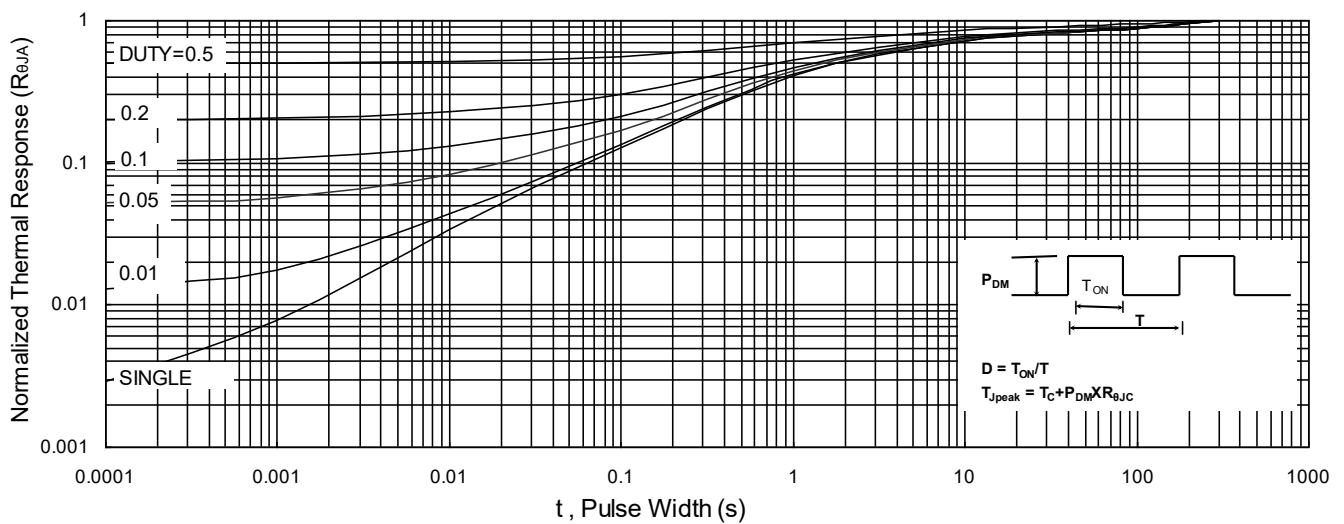


Fig.9 Normalized Maximum Transient Thermal Impedance

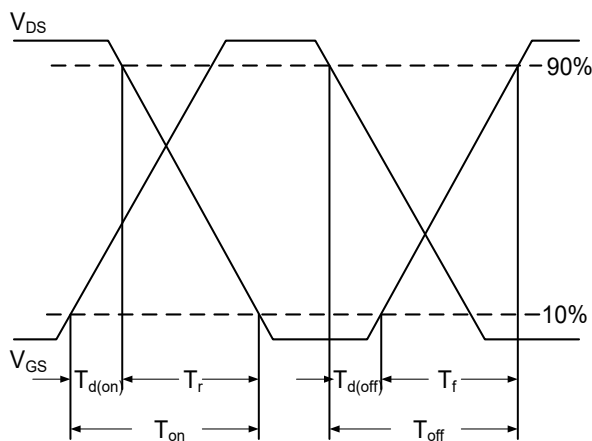


Fig.10 Switching Time Waveform

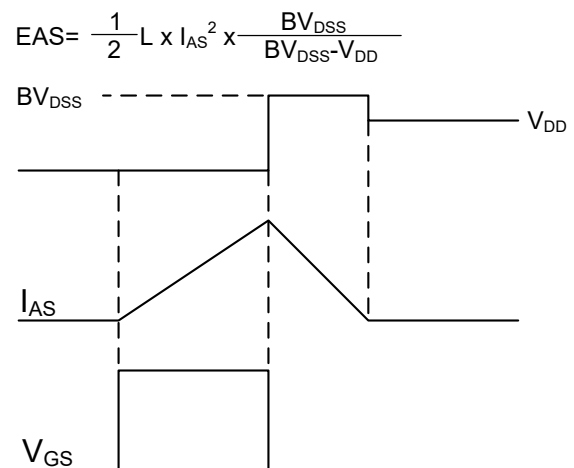


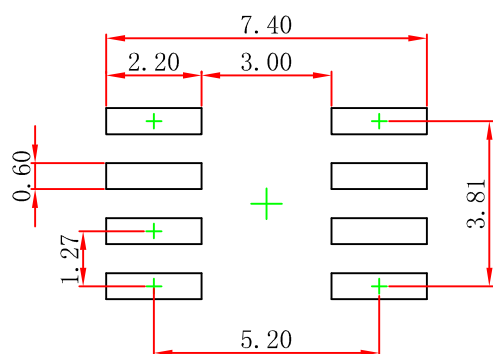
Fig.11 Unclamped Inductive Switching Waveform



## SOP-8(SO-8) Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



### Note:

1. Controlling dimension; in millimeters.
2. General tolerance:  $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.



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